

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("5759879").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/26 14:05
L2	4020	((257/64) or (257/66) or (257/71) or (345/92)).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/26 14:14
L3	51	2 and (personal adj computer laptop desktop) and ((mosfet mos misfet mesfet field adj effect adj transistor) and boundary near3 (crystal near3 grain) and (lattice near3 continuous\$2 continuity))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/26 14:16
L4	703	2 and (personal adj computer laptop desktop)"clm." and ((mosfet mos misfet mesfet field adj effect adj transistor)or (gate and drain and channel)).clm. and boundary near3 (crystal near3 grain).clm. and (lattice near3 continuous\$2 continuity).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/26 14:18
L5	1	2 and (personal adj computer laptop desktop).clm. and ((mosfet mos misfet mesfet field adj effect adj transistor)or (gate and drain and channel)).clm. and boundary near3 (crystal near3 grain).clm. and (lattice near3 continuous\$2 continuity).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/26 14:18
L6	0	2 and (personal adj computer laptop desktop).clm. and ((mosfet mos misfet mesfet field adj effect adj transistor)or (gate and drain and channel)).clm. and boundary near3 (crystal near3 grain).clm. and (lattice near3 continuous\$2 continuity).clm. and image.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/26 14:19

S7	0	(personal adj computer laptop desktop).clm. and ((mosfet mos misfet mesfet field adj effect adj transistor)or (gate and drain and channel)).clm. and boundary near (crystal near3 grain).clm. and ((lattice near3 continuous\$2 continuity).clm. and image.clm.	US-PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/26 14:19
S1	6	"753524".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/16 07:50
S2	1	S1 and grain adj boundary\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 15:09
S3	17	((5,170,244") or ("5,250,931") or ("5,525,822") or ("5,744,824") or ("5,780,872") or ("5,796,150") or ("5,821,138") or ("5,818,070") or ("5,821,622") or ("5,859,443") or ("5,864,150") or ("5,929,464") or ("5,942,768") or ("6,147,667") or ("6,211,536") or ("6,380,560") or ("20010018224")).PN	US-PGPUB; USPAT	OR	OFF	2005/03/14 15:09
S4	33	((5,170,244") or ("5,250,931") or ("5,525,822") or ("5,744,824") or ("5,780,872") or ("5,796,150") or ("5,821,138") or ("5,818,070") or ("5,821,622") or ("5,859,443") or ("5,864,150") or ("5,929,464") or ("5,942,768") or ("6,147,667") or ("6,211,536") or ("6,380,560") or ("20010018224")).PN	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/03/14 15:16
S5	10	ON-1116521\$-.did. JP-07135318\$-.did. JP-08078329\$-.did. JP-08213634\$-.did. JP-08288522\$-.did. JP-09022077\$-.did.	EPO; JPO; DERWENT	OR	OFF	2005/03/14 15:22
S6	4	JP-09312260\$-.did. JP-10270363\$-.did.	EPO; JPO; DERWENT	OR	OFF	2005/03/14 15:24
S7	44	S4 S5 S6	US-PGPUB; USPAT; USOOR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 15:24
S8	3	("6380560").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 16:28

S9	24	((5170244) or (5250931) or (5525822) or (5780872) or (5796150) or (5818070) or (5821138) or (5821622) or (5859443) or (5864150) or (5929464) or (6147667)).PN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 15:47
S10	719	grain adj boundar\$3 near6 (channel active) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 16:32
S11	488	grain adj boundar\$3 near6 (channel active) and (thin adj film adj transistor tft) and "257"/\$8.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 16:33
S12	27	lattice near10 grain adj boundar\$3 near6 (channel active) and (thin adj film adj transistor tft) and "257"/\$8.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 16:33
S13	3	void near10 grain adj boundar\$3 and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 17:01
S14	11	lattice adj defect near10 grain adj boundar\$3 and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 17:01
S15	47	(high adj resolution adj tem hitem high adj resolution adj2 electron adj microscopy) and grain adj boundar\$3 and (semiconductor near2 thin adj film tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 08:10
S16	33	(high adj resolution adj tem hitem high adj resolution adj2 electron adj microscopy) and ((trap void) near6 (grain adj boundar\$3)) and (semiconductor near2 thin adj film tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 08:11

S17	155	(tem hrtem electron adj microscopy) and ((trap void) near6 (grain adj boundar \$3)) and (semiconductor near2 thin adj film tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 08:12
S18	0	dangling adj bond near10 grain adj boundar\$3 and hydrogenated near3 (silicon si polysilicon) and (high adj resolution adj transmission adj electron adj microscopy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 09:11
S19	0	dangling adj bond near10 grain adj boundar\$3 and (high adj resolution adj transmission adj electron adj microscopy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 09:11
S20	36	dangling adj bond and (high adj resolution adj transmission adj electron adj microscopy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 09:11
S21	36	dangling adj bond and (high adj resolution adj transmission adj electron adj microscopy) and (silicon polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 09:11
S22	49	dangling adj bond and (high adj resolution adj transmission adj electron adj microscopy hrtem) and (silicon polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 09:45
S25	10	personal adj computer near10 (tft thin adj film adj transistor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 09:56
S26	1763	personal adj computer.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 09:57

S27	911	personal adj computer.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and liquid adj crystal adj display.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 09:58
S28	207	personal adj computer.ti. and (tft thin adj film adj transistor).ti,ab,clm. and liquid adj crystal adj display.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 09:58
S29	164	personal adj computer.ti. and (tft thin adj film adj transistor).ab. and liquid adj crystal adj display.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 10:04
S30	2	JP-08179306\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 10:25
S31	121	personal adj computer.ti. and (liquid adj crystal adj display/lcd) near10 (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 10:26
S32	119	S31 not yamazaki.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 10:40
S33	2	JP-08211367\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 10:49
S34	2	"5854627".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 10:55

S35	9114	(thin adj film adj transistor tft) and silicon and pixel adj electrode and (liquid adj crystal adj display lcd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 10:57
S36	188	(thin adj film adj transistor tft) and silicon and pixel adj electrode and (liquid adj crystal adj display lcd) and grain near3 orientation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 10:58
S37	8	(thin adj film adj transistor tft) and silicon and pixel adj electrode and (liquid adj crystal adj display lcd) and grain near3 orientation near6 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 10:58
S38	82	(US-20010018224-\$ or US-20020030190-\$ or US-20020040981-\$ or US-20020043682-\$ or US-20020070406-\$ or US-20020079484-\$ or US-20030001832-\$ or US-20030107077-\$ or US-20030211669-\$ or US-20040031986-\$ or US-20040080481-\$ or US-20040094765-\$ or US-20040164300-\$ or US-20040222424-\$).did. or (US-4352834-\$ or US-4392452-\$ or US-5170244-\$ or US-5250931-\$ or US-5525822-\$ or US-5744824-\$ or US-5780872-\$ or US-5796150-\$ or US-5818070-\$ or US-5821138-\$ or US-5821622-\$ or US-5859443-\$ or US-5864150-\$ or US-5929464-\$ or US-5942768-\$ or US-6147667-\$ or US-6211536-\$ or US-6303963-\$ or US-6323515-\$ or US-6335716-\$ or US-6380560-\$ or US-6462723-\$ or US-6472684-\$ or US-6509602-\$ or US-6597014-\$ or US-6597034-\$).did. or (US-6603453-\$ or US-6605497-\$ or US-6657494-\$ or US-6670635-\$ or US-6717179-\$ or US-6756640-\$ or US-6831727-\$ or US-693243-\$ or US-6066872-\$ or US-5879447-\$ or US-5712496-\$ or US-5582640-\$ or US-5854627-\$).did. or (JP-08078329-\$ or JP-08213634-\$ or JP-08288522-\$ or JP-09022077-\$ or JP-09312260-\$ or JP-10270363-\$ or JP-08211367-\$).did. or (EP-342925-\$ or EP-686308-\$ or JP-06317814-\$ or JP-07135318-\$ or JP-08006053-\$ or JP-080223100-\$ or JP-08078329-\$ or JP-08204207-\$ or JP-08213634-\$ or JP-08288522-\$ or JP-09022077-\$ or JP-09102613-\$ or JP-09312260-\$ or US-5796150-\$ or JP-10197897-\$ or JP-10209465-\$ or JP-10270363-\$ or JP-10303129-\$ or US-5859443-\$ or US-5864150-\$ or JP-08179306-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/15 13:18
S39	24	S38 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 13:24

S40	41	S38 and capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 13:26
S41	18	S38 and auxiliary adj (capacitance capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 13:35
S42	271	auxiliary adj (capacitance capacitor) near6 (LCD liquid adj crystal adj display)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 13:35
S43	195	auxiliary adj (capacitance capacitor) near6 (LCD liquid adj crystal adj display) and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 13:36
S44	136	auxiliary adj (capacitance capacitor) near4 (LCD liquid adj crystal adj display) and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 13:58
S45	13	channel near3 length and S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 14:08
S46	2413	channel near3 length and (tft thin adj film adj transistor).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 14:09
S47	640	channel adj length.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 14:09

S48	19	channel adj length.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and channel near4 length near4 (".mum." micron)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 14:12
S49	11	channel adj length.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and channel near4 length near4 (".mum." micron) and (liquid adj crystal adj display LCD)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/15 14:13
S50	6	"107113".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 15:03
S51	2005	257/66	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 15:03
S52	2420	257/72	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 15:03
S53	2853	257/59	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 15:03
S54	631	257/290	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 15:03
S55	1029	257/291	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 15:03

S56	998	257/292	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 15:04
S57	6444	S51 S52 S53 S54 S55 S56	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 15:04
S58	1479	345/92	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 15:08
S59	6450	S57 S58 and personal adj computer and (thin adj film adj transistor tft) and (liquid adj crystal adj display lcd) and grain adj (boundary boundaries) and (void dangling adj bond trap)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 15:10
S60	91	(S57 S58) and personal adj computer and (thin adj film adj transistor tft) and (liquid adj crystal adj display lcd) and grain adj (boundary boundaries) and (void dangling adj bond trap)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/15 15:11
S61	44	(US-20010018224-\$).did. or (US-6211536-\$ or US-6380560-\$ or US-5864150-\$ or US-6147667-\$ or US-5942768-\$ or US-5929464-\$ or US-5859443-\$ or US-5821622-\$ or US-5821138-\$ or US-5744824-\$ or US-5818070-\$ or US-5796150-\$ or US-5780872-\$ or US-5525822-\$ or US-5250931-\$ or US-5170244-\$).did. or (JP-08288522-\$ or JP-08213634-\$ or JP-09022077-\$ or JP-08078329-\$ or JP-09312260-\$ or JP-10270363-\$).did. or (US-5864150-\$ or US-5859443-\$ or JP-10303129-\$ or US-5796150-\$ or JP-10209465-\$ or JP-10197897-\$ or JP-08213634-\$ or JP-09102613-\$ or JP-08288522-\$ or JP-08023100-\$ or JP-08204207-\$ or JP-06317814-\$ or JP-08006053-\$ or EP-342925-\$ or EP-686308-\$ or EP-236629-\$ or JP-09022077-\$ or JP-08078329-\$ or JP-10270363-\$ or JP-07135318-\$ or JP-09312260-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/15 15:25
S62	6	"107113".ap.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/15 15:26

S63	372	easthom.xp.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/16 07:34
S64	6	"496953".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/16 07:39
S65	11	S63 and chip adj resistor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/16 07:44
S66	6	"107113".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/16 15:49
S67	163	(US-20010015441-\$ or US-20010018224-\$ or US-20010048108-\$ or US-20020011983-\$ or US-20020030190-\$ or US-20020040981-\$ or US-20020043682-\$ or US-20020053674-\$ or US-20020070406-\$ or US-20020079484-\$ or US-20020117736-\$ or US-20020125480-\$ or US-20020167051-\$ or US-20030001832-\$ or US-20030057419-\$ or US-20030062524-\$ or US-20030102480-\$ or US-20030107077-\$ or US-20030137480-\$ or US-20030141807-\$ or US-20030155573-\$ or US-20030160236-\$ or US-20030173567-\$ or US-20030186490-\$ or US-20030197179-\$ or US-20030201442-\$).did. or (US-20030211669-\$ or US-20030218169-\$ or US-20040026696-\$ or US-20040031986-\$ or US-20040080481-\$ or US-20040094765-\$ or US-20040164301-\$ or US-20040222424-\$).did. or (US-4352834-\$ or US-4392452-\$ or US-5170244-\$ or US-5250931-\$ or US-5525822-\$ or US-5582640-\$ or US-5712496-\$ or US-5744824-\$ or US-5780872-\$ or US-5796150-\$ or US-5818070-\$ or US-5821138-\$ or US-5821622-\$ or US-5854627-\$ or US-5859443-\$ or US-5864150-\$ or US-5879447-\$ or US-5929484-\$ or US-5942768-\$ or US-5999236-\$ or US-6066872-\$ or US-6087679-\$ or US-6093243-\$ or US-6140667-\$ or US-6147657-\$ or US-6160271-\$).did. or (US-6211536-\$ or US-6271818-\$ or US-6274887-\$ or US-6278131-\$ or US-6292183-\$ or US-6294815-\$ or US-6303963-\$ or US-6307214-\$ or US-6323515-\$ or US-6326249-\$ or US-6335716-\$ or US-6380007-\$ or US-6380560-\$ or US-6396105-\$ or US-6407430-\$ or US-6452211-\$ or US-6452341-\$ or US-6453637-\$ or US-6462723-\$ or US-6472684-\$ or US-6482684-\$ or US-6492659-\$ or US-6495886-\$ or US-6498369-\$ or US-6506669-\$ or US-6509602-\$ or US-6525719-\$).did. or (US-6531713-\$ or US-6534353-\$ or US-6545320-\$ or US-6549184-\$ or US-6576926-\$ or US-6583471-\$ or US-6590229-\$ or US-6590230-\$ or US-6593592-\$ or US-6597014-\$ or US-	OR	OFF	2005/03/17 15:29	

		6597034-\$ or US-6603435-\$ or US-6605497-\$ or US-6608324-\$ or US-6611022-\$ or US-6630977-\$ or US-6635929-\$ or US-6639244-\$ or US-6646288-\$ or US-6653657-\$ or US-6667494-\$ or US-6670835-\$ or US-6674136-\$ or US-6680487-\$ or US-6686228-\$ or US-6693044-\$ or US-6693299-\$).did. or (US-6693300-\$ or US-6703265-\$ or US-6717179-\$ or US-6727514-\$ or US-6730932-\$ or US-6737673-\$ or US-6738005-\$ or US-6756640-\$ or US-6762081-\$ or US-6777255-\$ or US-6777887-\$ or US-6784037-\$ or US-6787807-\$ or US-6806499-\$ or US-6822262-\$ or US-6825072-\$ or US-6831727-\$ or US-6841797-\$ or US-6844683-\$ or US-6855956-\$).did. or (JP-08078329-\$ or JP-08211367-\$ or JP-08213634-\$ or JP-08288522-\$ or JP-09022077-\$ or JP-09312260-\$ or JP-10270363-\$).did. or (EP-236629-\$ or EP-342925-\$ or EP-686308-\$ or JP-06317814-\$ or JP-07135318-\$ or JP-08006053-\$ or JP-08023100-\$ or JP-08078329-\$ or JP-08179306-\$ or JP-08204207-\$ or JP-08213634-\$ or JP-08288522-\$ or JP-09022077-\$ or JP-09102613-\$ or JP-09312260-\$ or US-5796150-\$ or JP-10197897-\$ or JP-10209465-\$ or JP-10270363-\$ or JP-10303129-\$ or US-5859443-\$ or US-5864150-\$).did.			
S68	4	S67 and okada.in.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF 2005/03/17 15:29
S69	3	"6730932".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF 2005/03/26 07:18
S70	491	pixel adj matrix adj circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF 2005/03/26 07:19
S71	460058	(liquid adj crystal adj display LCD liquid adj crystal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF 2005/03/26 07:19
S72	11	S70 not S71	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF 2005/03/26 07:20
S73	11	S72 not "349"/\$7.ocls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF 2005/03/26 07:36

S74	520	liquid adj crystal adj display near4 pixel adj electrode and personal adj computer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/26 07:38
S75	189	liquid adj crystal adj display near4 pixel adj electrode.ti,ab,clm. and personal adj computer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/26 07:38
S76	42	liquid adj crystal adj display near4 pixel adj electrode.ti,ab,clm. and personal adj computer.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/26 07:48
S77	3	"6380560",pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/26 07:45
S78	2	"5582640",pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/26 07:49
S79	2	jp-08211367\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/26 07:56
S80	2	jp-06230422\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/26 07:56
S81	2011	257/66	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/26 09:40

S82	2427	257/72	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/26 09:40
S83	2861	257/59	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/26 09:40
S84	631	257/290	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/26 09:40
S85	1031	257/291	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/26 09:40
S86	1004	257/292	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/26 09:40
S87	6466	S81 S82 S83 S84 S85 S86	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/26 09:40
S88	2	("5582640").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 21:23
S89	25	(metal\$3 near6 promot\$3 near6 crystalli\$5).clm. and semiconductor near1 energy. as. and (titanium tungsten tantalum molybdenum ti w ta mo).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 21:26

S90	6	(metal\$3 near6 promot\$3 near6 crystalli?S5).clm. and semiconductor near1 energy, as. and (titanium tungsten tantalum molybdenum ti w ta mo).clm. and contact, clm. and gate.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 21:29
S91	828	(metal\$3 near6 (further\$3 promot\$3 caus\$3 catalyst) near6 crystalli?S5) and (titanium tungsten tantalum molybdenum ti w ta mo) and contact and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 21:31
S92	209	(metal\$3 near6 (further\$3 promot\$3 caus\$3 catalyst) near6 crystalli?S5).ti,ab,clm. and (titanium tungsten tantalum molybdenum ti w ta mo) and contact and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 21:31
S93	200	(metal\$3 near6 (further\$3 promot\$3 caus\$3 catalyst) near6 crystalli?S5).ti,ab,clm. and (titanium tungsten tantalum molybdenum ti w ta mo) and contact and gate and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 21:32
S94	162	(metal\$3 near6 (further\$3 promot\$3 caus\$3 catalyst) near6 crystalli?S5).ti,ab,clm. and (titanium tungsten tantalum molybdenum ti w ta mo) and contact and gate and (thin adj film adj transistor tft) and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 21:34
S95	119	(metal\$3 near6 (further\$3 promot\$3 caus\$3 catalyst) near6 crystalli?S5).ti,ab,clm. and (titanium tungsten tantalum molybdenum ti w ta mo) and contact and gate and (thin adj film adj transistor tft).ti,ab,clm. and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 21:34
S96	1	(US-20040164300-\$).did.	US-PGPUB	OR	OFF	2006/05/19 09:01
S97	2	("5582640").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/19 09:01
S98	1	S97 and grain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 09:02

S99	1	S97 and grain near2 boundary	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2006/05/19 09:19
S100	4	(("5481121") or ("5824573")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	OFF	2006/05/19 09:19
S101	2	jp-07074366\$-\$did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	OFF	2006/05/19 09:21
S102	21	(("20020053670") or ("5,569,610") or ("5,569,936") or ("5,595,923") or ("5,614,733") or ("5,643,826") or ("5,783,468") or ("5,789,762") or ("5,858,823") or ("5,923,962") or ("6285042") or ("6,335,541") or ("6,642,073")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	OFF	2006/05/19 09:24
S103	13	(("20020053670") or ("5,569,610") or ("5,569,936") or ("5,595,923") or ("5,614,733") or ("5,643,826") or ("5,783,468") or ("5,789,762") or ("5,858,823") or ("5,923,962") or ("6285042") or ("6,335,541") or ("6,642,073")).PN.	US-PGPUB; USPAT	OR	OFF	2006/05/19 09:25
S104	8	EP-0651431\$-\$did. EP-1158580\$-\$did. jp-08078690\$-\$did. jp-09045931\$-\$did. jp-09092834\$-\$did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2006/05/19 09:37
S105	0	EP-0651431\$-\$did. EP-1158580\$-\$did. jp-08078690\$-\$did. jp-09045931\$-\$did. jp-09092834\$-\$did.	US-PGPUB; USPAT	OR	ON	2006/05/19 09:37
S106	7	EP-0651431\$-\$did. EP-1158580\$-\$did. jp-08078690\$-\$did. jp-09045931\$-\$did. jp-09092834\$-\$did.	JPO; DERWENT	OR	ON	2006/05/19 09:38
S107	7	EP-0651431\$-\$did. EP-1158580\$-\$did. jp-08078690\$-\$did. jp-09045931\$-\$did. jp-09092834\$-\$did. jp-07074366\$-\$did.	JPO; DERWENT	OR	ON	2006/05/19 09:39
S108	9	EP-0651431\$-\$did. EP-1158580\$-\$did. jp-08078690\$-\$did. jp-09045931\$-\$did. jp-09092834\$-\$did. jp-07074366\$-\$did.	JPO; DERWENT	OR	ON	2006/05/19 09:52
S109	9	EP-0651431\$-\$did. EP-1158580\$-\$did. jp-08078690\$-\$did. jp-09045931\$-\$did. jp-09092834\$-\$did. jp-07074366\$-\$did.	JPO; DERWENT	OR	ON	2006/05/19 09:53
S110	14	EP-0651431\$-\$did. EP-1158580\$-\$did. jp-08078690\$-\$did. jp-09045931\$-\$did. jp-09092834\$-\$did. jp-07074366\$-\$did. jp-07130652\$-\$did. jp-06318701\$-\$did. jp-06268212\$-\$did.	JPO; DERWENT	OR	ON	2006/05/19 09:55

S111	14	EP-06051431\$-.did. EP-1158580\$-.did. jp-08078690\$-.did. jp-09045931\$-.did. jp-09092834\$-.did. jp-07074366\$-.did. jp-07130652\$-.did. jp-06318701\$-.did. jp-06268212\$-.did. jp-07130652\$-.did.	JPO; DERWENT	OR	ON	2006/05/19 09:56
S112	14	EP-06051431\$-.did. EP-1158580\$-.did. jp-08078690\$-.did. jp-09045931\$-.did. jp-09092834\$-.did. jp-07074366\$-.did. jp-07130652\$-.did. jp-06318701\$-.did. jp-06268212\$-.did.	JPO; DERWENT	OR	ON	2006/05/19 09:56
S113	1	jp-07130652\$-.did.	JPO; DERWENT	OR	ON	2006/05/19 10:28
S114	4	grain adj boundary near4 continuous\$2 near4 connect\$3	JPO; DERWENT	OR	ON	2006/05/19 10:30
S115	74	grain adj boundary near4 continuous\$2 near4 connect\$3	US_PGPUB; USPAT; USOOR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 10:30
S116	71	(grain adj boundary near4 continuous\$2 near4 connect\$3) and semiconductor	US_PGPUB; USPAT; USOOR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 10:31
S117	20	(grain adj boundary near4 continuous\$2 near4 connect\$3) with semiconductor	US_PGPUB; USPAT; USOOR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 10:36
S118	32	(grain adj boundary near4 continuous\$2 near4 connect\$3) same semiconductor	US_PGPUB; USPAT; USOOR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 10:38
S119	1	(grain adj boundary near4 continuous\$2 near4 connect\$3) same photograph same (semiconductor silicon)	US_PGPUB; USPAT; USOOR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 10:53

S120	45	(grain adj boundary near4 photograph) same (semiconductor silicon)	US-PGPUB; USPAT; USOOR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 10:54
S121	0	("grainadjboundarynear4(directdirectionorientationorient) andsemiconductorsiliconand (transistormosfettnmosfetpmosfetmisfetnmisfetpmisfet)".PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/19 13:03
S122	381	grain adj boundary near4 (direct direction orientation orient) and (semiconductor silicon) and (transistor mosfet tft nmosfet pmosfet misfet nmisfet pmisfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/19 13:15
S123	228	S122 not semiconductor adj energy,as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/19 13:15
S124	120	S122 not semiconductor adj energy,as.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/19 13:20
S125	2	jp-08288515\$-\$,DID.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/19 13:21
S126	2	("5759879"),PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/19 17:44
S127	2	S126 and grain adj boundary	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 13:56

S128	0	S126 and grain adj boundary and computer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 13:56
S129	4200	tft and personal adj computer and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 17:48
S130	991	tft and personal adj computer.ti,ab,clm. and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 17:48
S131	2	("5759879").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/20 17:57
S132	0	S131 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/20 17:57
S133	1	"5639698".PN.	USPAT; USOCR	OR	OFF	2006/05/20 17:57
S134	1	"5549747".PN.	USPAT; USOCR	OR	OFF	2006/05/20 18:00
S135	1	"5531182".PN.	USPAT; USOCR	OR	OFF	2006/05/20 18:00
S136	1	"4933298".PN.	USPAT; USOCR	OR	OFF	2006/05/20 18:02
S137	1	"4381202".PN.	USPAT; USOCR	OR	OFF	2006/05/20 18:04
S138	4	capacitor.ti,ab,clm. and (thin adj film adj transistor tft).ti,ab,clm. and personal adj computer.ti,ab,clm. and @ad<"19960101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 18:08

S139	8	capacitor and (thin adj film adj transistor tft) and personal adj computer.ti,ab,clm. and @ad<"19960101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 18:12
S140	8	capacitor and (thin adj film adj transistor tft) and personal adj computer.ti,ab,clm. and personal adj computer and @ad<"19960101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 18:12
S141	2	("5250931").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/20 18:28
S142	0	("active adj matrix adj display with capacitor with tft and (personal adj computer PC)").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/20 18:28
S143	17	active adj matrix adj display with capacitor with tft and (personal adj computer PC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 18:30
S144	37	active adj matrix adj display same capacitor same tft and (personal adj computer PC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 19:39
S145	4	(active adj matrix adj display) same (pixel adj electrode) same (bottom adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 19:41
S146	54	(active adj matrix adj display) and (pixel adj electrode) and (bottom adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 19:42

S147	8	(active adj matrix adj display) and (pixel adj electrode) and (bottom adj electrode) and short adj channel and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 19:43
S148	11	(active adj matrix adj display) and (pixel adj electrode) and (common adj electrode) and short adj channel and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 20:26
S149	28	"5539219"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 20:27
S150	62	den adj boer.in. and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 20:45
S151	7113	((257/59) or (257/66) or (257/72) or (257/290) or (257/291) or (257/292) or (345/92)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/20 20:57
S152	3080	((257/64) or (257/66) or (257/71) or (345/92)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/20 20:57
S153	165	S152 and thin adj film adj transistor and capacitor and active adj matrix and liquid adj crystal and grain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 20:59
S154	31	S152 and thin adj film adj transistor and capacitor and active adj matrix and liquid adj crystal and grain and @ad<"19970121"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 21:00

S155	5	"6607012"	US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB	OR	OFF	2006/05/21 17:00
S156	6	"405053".ap.	US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB	OR	OFF	2006/05/22 11:12
S157	236	(US-20040164300-\$ or US-20010018224-\$ or US-20030141807-\$ or US-20030218169-\$ or US-20030201442-\$ or US-20030062524-\$ or US-20020053674-\$ or US-20040222424-\$ or US-20040080481-\$ or US-20040031986-\$ or US-20030211669-\$ or US-20030107077-\$ or US-20020079484-\$ or US-20020070406-\$ or US-20020040981-\$ or US-20040094765-\$ or US-20030001832-\$ or US-20020030190-\$ or US-20020043682-\$ or US-20020125480-\$ or US-20030173567-\$ or US-20020117736-\$ or US-20040026696-\$ or US-20030186490-\$ or US-20030155573-\$ or US-20030137480-\$).did. or (US-20030197179-\$ or US-20030057419-\$ or US-20030102480-\$ or US-20010048108-\$ or US-20020167051-\$ or US-20020011983-\$ or US-20030160236-\$ or US-20010015441-\$ or US-20020053670-\$).did. or (US-6147667-\$ or US-6380560-\$ or US-6211536-\$ or US-5942768-\$ or US-5821622-\$ or US-5929464-\$ or US-5864150-\$ or US-5859443-\$ or US-5821138-\$ or US-5744824-\$ or US-5818070-\$ or US-5795150-\$ or US-5780872-\$ or US-5250931-\$ or US-5525822-\$ or US-5170244-\$ or US-6703265-\$ or US-5595923-\$ or US-6841797-\$ or US-6762081-\$ or US-6738005-\$ or US-6653657-\$ or US-6611022-\$ or US-6534853-\$ or US-6506669-\$ or US-6492659-\$).did. or (US-6396105-\$ or US-6380007-\$ or US-6292183-\$ or US-6831727-\$ or US-6756640-\$ or US-6717179-\$ or US-6670635-\$ or US-6605497-\$ or US-6603453-\$ or US-6597014-\$ or US-6509602-\$ or US-6472884-\$ or US-6462723-\$ or US-6323515-\$ or US-5824573-\$ or US-6597034-\$ or US-6657494-\$ or US-4392452-\$ or US-5481121-\$ or US-6335716-\$ or US-6303963-\$ or US-4352834-\$ or US-6730932-\$ or US-6680487-\$ or US-6646288-\$ or US-6593592-\$ or US-6452211-\$).did. or (US-6294815-\$ or US-6093243-\$ or US-6066872-\$ or US-6693300-\$ or US-6693299-\$ or US-6498369-\$ or US-6635929-\$ or US-6326249-\$ or US-5879447-\$ or US-5582640-\$ or US-6855956-\$ or US-6844683-\$ or US-6825072-\$ or US-6777887-\$ or US-6777255-\$ or US-6727514-\$ or US-6674136-\$ or US-6630977-\$ or US-6590230-\$ or US-6590229-\$ or US-6322262-\$ or US-6784037-\$ or US-6576926-\$ or US-6549184-\$ or US-6531713-\$ or US-6495886-\$ or US-6452341-\$).did. or (US-6278131-\$ or US-6686228-\$ or US-6639244-\$ or US-6583471-\$ or US-6608324-\$ or US-6545320-\$ or US-6274887-\$ or US-6140667-\$ or US-6087679-\$ or US-5712496-\$ or US-6307214-\$ or US-6407430-\$ or US-6160271-\$ or US-5854627-\$ or US-6787807-\$ or US-5569936-\$ or US-6806499-\$ or US-6693044-\$ or US-6525719-\$ or US-6737673-\$ or US-6458637-\$ or US-5999236-\$ or US-6482684-\$ or US-6271818-\$ or US-6744069-\$ or US-6642073-\$ or US-6319761-\$).did. or (US-5581092-\$ or US-6335541-\$ or US-5923962-\$ or US-5858923-\$ or US-	US-PGPUB; USPAT; JPO; DERVENT	OR	OFF	2006/05/22 11:12

		5789762-\$ or US-5643826-\$ or US-5614733-\$ or US-5569610-\$ or US-6285042-\$ or US-5783468-\$ or US-6093934-\$ or US-5534716-\$ or US-5661050-\$ or US-5539219-\$ or US-5641974-\$ or US-5614427-\$ or US-5656824-\$ or US-6650358-\$ or US-6528820-\$ or US-6028333-\$ or US-5949091-\$ or US-5854494-\$ or US-5821559-\$ or US-5808321-\$ or US-5736751-\$ or US-5705829-\$ or US-5698864-\$). did. or (US-5680147-\$ or US-5563426-\$ or US-5554861-\$ or US-5543947-\$ or US-5508216-\$ or US-5414278-\$ or US-5403772-\$ or US-5289030-\$ or US-5206749-\$ or US-5165075-\$ or US-4623908-\$ or US-5523587-\$ or US-5744823-\$ or US-5583369-\$ or US-5218464-\$ or US-4582395-\$). did. or (JP-09022077-\$ or JP-08213634-\$ or JP-08078329-\$ or JP-08288522-\$ or JP-10270363-\$ or JP-09312260-\$ or JP-08211367-\$ or JP-06230422-\$ or JP-09092834-\$ or JP-09045931-\$ or JP-08078690-\$ or JP-07074366-\$ or JP-06318701-\$ or JP-06268212-\$ or JP-08288515-\$ or JP-06310456-\$). did. or (US-5864150-\$ or JP-10303129-\$ or US-5859443-\$ or JP-10209465-\$ or US-5796150-\$ or JP-10197897-\$ or JP-08213634-\$ or JP-09102613-\$ or JP-08204207-\$ or JP-08288522-\$ or JP-08006053-\$ or JP-08023100-\$ or EP-342925-\$ or JP-06317814-\$ or EP-686308-\$ or EP-236629-\$ or JP-09022077-\$ or JP-08078329-\$ or JP-07135318-\$ or JP-10270363-\$ or JP-09312260-\$ or US-5824573-\$ or JP-08211367-\$ or JP-08179306-\$ or JP-06230422-\$ or EP-1158580-\$). did. or (JP-09092834-\$ or JP-09045931-\$ or JP-08078690-\$ or EP-651431-\$ or JP-06268212-\$ or US-5481121-\$ or JP-06318701-\$ or JP-08288515-\$ or EP-669647-\$). did.			
S158	0	S157 and wang.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF 2006/05/22 11:13
S159	0	("20030153155.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF 2006/05/22 11:14
S160	2	("20030153155").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF 2006/05/22 11:14
S161	0	("jp-8288515\$\$did.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF 2006/10/03 14:51

S162	2	jp-08288515\$-\$did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/03 16:02
S163	3	"318899".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 17:29
S164	2	jp-08288515\$-\$did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/15 19:01
S165	2	("5759879").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/15 19:22
S166	2	("5539219").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/15 19:13
S167	174	(silicon near2 shape near2 crystal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/15 19:34
S168	7	rod\$1shape\$1 near2 crystal near2 (silicon si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/15 19:40
S169	2	("6828587").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/15 19:42

S170	26	rod-shaped near1 crystal same silicon	US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB	OR	ON	2007/04/15 21:10
S171	25366	(lightly adj doped adj drain LDD)	US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB	OR	ON	2007/04/15 21:10
S172	238	(US-20020117736-\$ or US-20040222424-\$ or US-20030141807-\$ or US-20020053674-\$ or US-20030186490-\$ or US-20010015441-\$ or US-20030160236-\$ or US-20030201442-\$ or US-2002011983-\$ or US-20020167051-\$ or US-20010018224-\$ or US-20040164300-\$ or US-20030062524-\$ or US-20020125480-\$ or US-20030211669-\$ or US-20030057419-\$ or US-20030107077-\$ or US-20030001832-\$ or US-20020079484-\$ or US-20020070406-\$ or US-20020043682-\$ or US-20040026696-\$ or US-20020040981-\$ or US-20020030190-\$ or US-20010048108-\$ or US-20030218169-\$).did. or (US-20030197179-\$ or US-20030155573-\$ or US-20030137480-\$ or US-20030102480-\$ or US-20030173567-\$ or US-20040080481-\$ or US-20040031986-\$ or US-20040094765-\$ or US-20020053670-\$).did. or (US-6841797-\$ or US-5854627-\$ or US-6762081-\$ or US-5569936-\$ or US-5999236-\$ or US-6278131-\$ or US-8271818-\$ or US-6646288-\$ or US-5549184-\$ or US-6703265-\$ or US-6452211-\$ or US-6482684-\$ or US-6525719-\$ or US-6303963-\$ or US-6458637-\$ or US-6693300-\$ or US-5170244-\$ or US-5250931-\$ or US-5525822-\$ or US-5744824-\$ or US-5780872-\$ or US-5796150-\$ or US-5818070-\$ or US-5821138-\$ or US-5821622-\$ or US-5859443-\$).did. or (US-5864150-\$ or US-5929464-\$ or US-5942768-\$ or US-6147667-\$ or US-6211536-\$ or US-6380560-\$ or US-5595923-\$ or US-6534353-\$ or US-6307214-\$ or US-6777255-\$ or US-6777887-\$ or US-6593592-\$ or US-6635929-\$ or US-6498369-\$ or US-6452341-\$ or US-4392452-\$ or US-6680487-\$ or US-6730932-\$ or US-6831727-\$ or US-6756640-\$ or US-6087679-\$ or US-6727514-\$ or US-6326249-\$ or US-6274887-\$ or US-6855956-\$ or US-6294815-\$ or US-6093243-\$).did. or (US-6066872-\$ or US-6531713-\$ or US-6160271-\$ or US-6140667-\$ or US-5879447-\$ or US-6806499-\$ or US-6674136-\$ or US-4352834-\$ or US-6492659-\$ or US-6407430-\$ or US-6653657-\$ or US-6495886-\$ or US-6292183-\$ or US-6611022-\$ or US-6693299-\$ or US-6380007-\$ or US-6787807-\$ or US-6396105-\$ or US-6506669-\$ or US-6738005-\$ or US-6886228-\$ or US-5712496-\$ or US-6590229-\$ or US-6583471-\$ or US-6597014-\$ or US-6822262-\$ or US-6576926-\$).did. or (US-6784037-\$ or US-6509602-\$ or US-6472684-\$ or US-6462723-\$ or US-6335716-\$ or US-6323515-\$ or US-630977-\$ or US-6545320-\$ or US-6608324-\$ or US-5582640-\$ or US-6717179-\$ or US-6844683-\$ or US-6590230-\$ or US-6825072-\$ or US-6670635-\$ or US-6657494-\$ or US-6605497-\$ or US-6603453-\$ or US-6597034-\$ or US-6693044-\$ or US-6633944-\$ or US-6737673-\$ or US-6744069-\$ or US-6642073-\$ or US-5581092-\$ or US-6319761-\$ or US-6335541-\$).did. or (US-6285042-\$ or US-5789762-\$ or US-5783468-\$ or US-5614733-\$ or US-	US-PGPUB; USPAT; JPO; DERVENT	OR	OFF	2007/04/15 21:11

		5569610-\$ or US-5824573-\$ or US-5481121-\$ or US-5923962-\$ or US-5858823-\$ or US-5643826-\$ or US-6093934-\$ or US-5534716-\$ or US-5661050-\$ or US-5539219-\$ or US-5614427-\$ or US-5656824-\$ or US-5650358-\$ or US-5641974-\$ or US-6528820-\$ or US-6026333-\$ or US-5949091-\$ or US-5854494-\$ or US-5821559-\$ or US-5808321-\$ or US-5554861-\$ or US-5523587-\$ or US-5508216-\$), did. or (US-5414278-\$ or US-5289030-\$ or US-5218464-\$ or US-5206749-\$ or US-5165075-\$ or US-4623908-\$ or US-4582395-\$ or US-5744823-\$ or US-5736751-\$ or US-5705829-\$ or US-5698864-\$ or US-5680147-\$ or US-5583369-\$ or US-5563426-\$ or US-5543947-\$ or US-5403772-\$ or US-5759879-\$ or US-3925903-\$), did. or (JP-09312260-\$ or JP-10270363-\$ or JP-08078329-\$ or JP-08213634-\$ or JP-08288522-\$ or JP-09022077-\$ or JP-08211367-\$ or JP-06230422-\$ or JP-07074366-\$ or JP-09045931-\$ or JP-06318701-\$ or JP-06268212-\$ or JP-09092834-\$ or JP-08078690-\$ or JP-08288515-\$ or JP-06310456-\$), did. or (JP-09312260-\$ or JP-06230422-\$ or US-5824573-\$ or US-5481121-\$ or JP-08179306-\$ or JP-10270363-\$ or JP-08078329-\$ or JP-09022077-\$ or JP-07135318-\$ or JP-08211367-\$ or EP-236629-\$ or EP-342925-\$ or EP-686308-\$ or JP-06317814-\$ or JP-08006053-\$ or JP-08023100-\$ or JP-08204207-\$ or JP-08213634-\$ or JP-08288522-\$ or JP-09102613-\$ or JP-10197897-\$ or JP-10209465-\$ or US-5796150-\$ or JP-10303129-\$ or US-5859443-\$ or US-5864150-\$), did. or (EP-1158580-\$ or JP-09092834-\$ or JP-09045931-\$ or EP-651431-\$ or JP-06318701-\$ or JP-08078690-\$ or JP-06268212-\$ or EP-669647-\$ or JP-08288515-\$), did.				
S173	89	S171 and S172	US_PGPUB; USPAT; JPO; DERWENT	OR	OFF	2007/04/15 21:11
S174	5094	odd and tft	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/16 07:50
S175	2802	S174 not (semiconductor adj energy.as.)	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/16 07:51
S176	131	S174 not (semiconductor adj energy.as.) and channel near4 mobility	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/16 07:51
S177	88	S174 not (semiconductor adj energy.as.) and channel near4 mobility and (polycrystal polycrystalline) near3 (silicon si)	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/16 08:36

S178	3443	((257/64) or (257/66) or (257/71) or (345/92)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/16 08:36
S179	43	S178 and personal adj computer.ti,ab,clm. and grain and lattice and (semiconductor adj (film thin adj film) thin adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/16 08:40
S180	10	((semiconductor adj energy).as. (shunpei near1 yamazaki).in. (hisashi near1 (ohtani otani).in.) and personal adj computer.clm. and grain.clm. and lattice.clm. and (semiconductor adj (film thin adj film) thin adj film).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/16 08:42
S181	2	"5759879".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/24 12:10
S182	768	grain adj boundary and (photograph image) and channel and (recrystall?ation recrystall?ing recrystall?e\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 12:12
S183	672	grain adj boundary and (photograph image) and channel and (recrystall?ation recrystall?ing recrystall?e\$1) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 12:13
S184	23	grain adj boundary near20 (photograph image) and channel and (recrystall?ation recrystall?ing recrystall?e\$1) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 12:23
S185	16	grain adj boundary near20 (photograph image) near20 (channel semiconductor adj film) and (semiconductor silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 14:05

S186	7	(grain adj boundary near3 (polycrystalline adj silicon polysilicon)) near10 (image photograph photographic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 14:10
S187	23	(grain adj boundary near3 (polycrystalline adj silicon polysilicon)) same (image photograph photographic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 14:14
S188	2	"5940464".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 14:19
S189	1	(image photograph) near5 grain adj boundary near5 polysilicon and @ad<"19980101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 14:20
S190	165	(image photograph) near5 polysilicon and @ad<"19980101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 16:28
S191	26	grain adj size near5 polysilicon near20 (image photograph SEM TEM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 16:32
S192	32	grain adj size near5 (poly-Si polysilicon) near20 (image photograph SEM TEM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 18:48
S193	12	(("4381202") or ("4933298") or ("5531182") or ("5549747") or ("5637515") or ("5639698")),PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/24 19:03

S194	2914	silicon adj wafer and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/24 19:03
S195	302	silicon adj wafer and thin adj film adj transistor.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 19:04
S196	52	silicon adj wafer and thin adj film adj transistor.ti. and @ad<"19970101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/24 19:04
S197	1	(US-20040164300-\$).did.	US-PGPUB	OR	ON	2008/03/29 21:40
S198	1	S197 and correspond\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/29 21:40
S199	76317	(tft thin adj film adj transistor).ti,ab,clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/29 21:52
S200	2586	(tft thin adj film adj transistor).ti,ab,clm. and (grain adj boundary)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/29 21:52
S201	195	(tft thin adj film adj transistor).ti,ab,clm. and (grain adj boundary) near10 (dangling adj bond)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/29 21:53

S202	48	(tft thin adj film adj transistor).ti,ab,clm. and (grain adj boundary) near10 (dangling adj bond) and @ad<"19970121"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/29 21:56
S203	0	(US-20040164300-\$).did. and semiconductor adj film and channel adj formation and source and drain and gate adj electrode and first adj crystal and second adj crystal	US-PGPUB	OR	ON	2008/03/29 22:35
S204	1	(US-20040164300-\$).did. and semiconductor adj film and channel adj formation and source and drain and gate adj electrode and crystal	US-PGPUB	OR	ON	2008/03/29 22:35
S205	2	("5830538").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/29 22:48
S206	0	S205 and dangling	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/29 22:52
S207	2	"5830538".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/30 09:45
S208	3425	d-spacing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/30 09:45
S209	1	S207 and S208	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/30 09:45

S210	12	d-spacing.ti.	US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB	OR	ON	2008/03/30 09:47
S211	12	d-spacing.ti. and d-spacing	US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB	OR	ON	2008/03/30 09:47
S212	243	(US-20040164300-\$ or US-20010018224-\$ or US-20020167051-\$ or US-20030218169-\$ or US-20030160236-\$ or US-20020053674-\$ or US-2002011983-\$ or US-20040094765-\$ or US-20040080481-\$ or US-20040031986-\$ or US-20030107077-\$ or US-20030001832-\$ or US-20020079484-\$ or US-20020070406-\$ or US-20020043682-\$ or US-20020040981-\$ or US-20040222424-\$ or US-20030211669-\$ or US-20020030190-\$ or US-20030173567-\$ or US-20020125480-\$ or US-20020117736-\$ or US-20030186490-\$ or US-20030155573-\$ or US-20030102480-\$ or US-20030057419-\$).did. or (US-20010048108-\$ or US-20040026695-\$ or US-20030197179-\$ or US-20030137480-\$ or US-20030141807-\$ or US-200302011442-\$ or US-20030062524-3 or US-20010015441-\$ or US-20020053670-\$ or US-20060134840-\$).did. or (US-6335541-\$ or US-6380560-\$ or US-6147657-\$ or US-5942768-\$ or US-6211536-\$ or US-5864150-\$ or US-5821622-\$ or US-5929464-\$ or US-5818070-\$ or US-5796150-\$ or US-5859443-\$ or US-5744824-\$ or US-5821138-\$ or US-5525822-\$ or US-5780872-\$ or US-5170244-\$ or US-5250931-\$ or US-5854627-\$ or US-6787807-\$ or US-6703265-\$ or US-6762081-\$ or US-6738005-\$ or US-6693044-\$ or US-6611022-\$ or US-6534353-\$ or US-6525719-\$).did. or (US-6492659-\$ or US-6458637-\$ or US-6396105-\$ or US-6292183-\$ or US-6271818-\$ or US-6831727-\$ or US-6717179-\$ or US-6667494-\$ or US-6603453-\$ or US-6597014-\$ or US-6472684-\$ or US-6755640-\$ or US-6670635-\$ or US-6462723-\$ or US-6335716-\$ or US-6323515-\$ or US-6303963-\$ or US-6597034-\$ or US-6605497-\$ or US-6509602-\$ or US-4392452-\$ or US-6730832-\$ or US-6693300-\$ or US-6693299-\$ or US-6680487-\$ or US-6646288-\$ or US-4352834-\$).did. or (US-6593592-\$ or US-6452211-\$ or US-6326249-\$ or US-6093243-\$ or US-6635929-\$ or US-6498369-\$ or US-5582640-\$ or US-6294815-\$ or US-5879447-\$ or US-6068872-\$ or US-6844683-\$ or US-6825072-\$ or US-6784037-\$ or US-6777255-\$ or US-6727514-\$ or US-66886228-\$ or US-6855956-\$ or US-6777887-\$ or US-6822262-\$ or US-66393244-\$ or US-6630977-\$ or US-6590230-\$ or US-6590229-\$ or US-6576926-\$ or US-6549184-\$ or US-6545320-\$ or US-6674136-\$).did. or (US-6583471-\$ or US-6608324-\$ or US-6495886-\$ or US-6407430-\$ or US-6278131-\$ or US-6160271-\$ or US-6140687-\$ or US-6087679-\$ or US-6452341-\$ or US-6531713-\$ or US-6307214-\$ or US-6274887-\$ or US-5712496-\$ or US-5595923-\$ or US-5569936-\$ or US-6841797-\$ or US-6806499-\$ or US-6737673-\$ or US-6653657-\$ or US-6482684-\$ or US-6506669-\$ or US-6380007-\$ or US-5999236-\$ or US-6744069-\$ or US-6642073-\$ or US-6319761-\$ or US-5581092-\$).did. or (US-5923962-\$ or US-5789762-\$ or US-	US-PGPUB; USPAT; JPO; DERVENT	OR	ON	2008/03/30 10:01

		5783468-\$ or US-5643826-\$ or US-5556910-\$ or US-5481121-\$ or US-5824573-\$ or US-6285042-\$ or US-5858823-\$ or US-5614733-\$ or US-6093934-\$ or US-5759879-\$ or US-5534716-\$ or US-5681050-\$ or US-5656824-\$ or US-5650358-\$ or US-5641974-\$ or US-5614427-\$ or US-5539219-\$ or US-6528820-\$ or US-6028333-\$ or US-5949091-\$ or US-5854494-\$ or US-5808321-\$ or US-5744823-\$ or US-5736751-\$ or US-5698864-\$).did. or (US-5680147-\$ or US-5563426-\$ or US-5554861-\$ or US-5543947-\$ or US-5523887-\$ or US-5508216-\$ or US-5414278-\$ or US-5289030-\$ or US-5218464-\$ or US-5206749-\$ or US-5165075-\$ or US-4829908-\$ or US-4592395-\$ or US-5705829-\$ or US-5921559-\$ or US-5933369-\$ or US-5403772-\$ or US-3925803-\$ or US-5923964-\$ or US-5904513-\$ or US-5869360-\$ or US-5753543-\$).did. or (JP-09022077-\$ or JP-08288522-\$ or JP-08213634-\$ or JP-08078329-\$ or JP-10270363-\$ or JP-09312260-\$ or JP-08211367-\$ or JP-06230422-\$ or JP-09092834-\$ or JP-09045931-\$ or JP-06318701-\$ or JP-06268212-\$ or JP-07074366-\$ or JP-08078690-\$ or JP-08288515-\$ or JP-06310456-\$).did. or (US-5864150-\$ or US-5859443-\$ or JP-10303129-\$ or US-5796150-\$ or JP-10209465-\$ or JP-08023100-\$ or JP-08006053-\$ or JP-10197897-\$ or JP-09102613-\$ or JP-08288522-\$ or JP-08213634-\$ or JP-08204207-\$ or JP-06317814-\$ or JP-08078329-\$ or EP-686308-\$ or EP-342925-\$ or JP-10270363-\$ or JP-09312260-\$ or EP-236629-\$ or JP-09022077-\$ or JP-07135318-\$ or JP-08211367-\$ or US-5481121-\$ or JP-08179306-\$ or JP-06230422-\$ or EP-1158580-\$).did. or (JP-09092834-\$ or JP-09045931-\$ or JP-06268212-\$ or JP-06318701-\$ or EP-651431-\$ or US-5824573-\$ or JP-08078690-\$ or JP-08288515-\$ or EP-659647-\$).did.				
S213	0	S212 and gosain.in.	US-PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/30 10:02
S214	2	("5,759,879"), PN.	US-PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/30 10:08
S215	8	laser near3 annealing and thin adj film adj transistor.ti. and hydrogenation near4 (dangling adj bonds)	US-PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/30 10:33

S216	1	"5567633",pn. and laser and hydrogenal\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/30 10:36
S217	1	(US-20040164300-\$).did.	US-PGPUB	OR	ON	2008/03/30 10:56
S218	1	(US-20040164300-\$).did. and (correspond correspondence) near20 dangling	US-PGPUB	OR	ON	2008/03/30 10:57
S219	3	(("6730932") or ("6380560")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/30 11:15
S220	2	("6380560").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/30 11:39
S221	3804	((257/64) or (257/66) or (257/71) or (345/92)).COLS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/30 12:03
S222	0	S221 and (personal adj computer PC) and (semiconductor silicon) adj (film layer) and source and drain and gate and lattice and crystal and dangling	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/30 12:04
S223	94	S221 and (personal adj computer PC) and (semiconductor silicon) adj (film layer) and source and drain and gate and lattice and crystal and dangling	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/30 12:04

S224	0	((ohtani near1 hisashi).in. (yamazaki near1 shunpe).in. (semiconductor near1 energy).as.) and (personal adj computer PC).clm. and (semiconductor silicon) adj (film layer).clm. and source.clm. and drain.clm. and gate.clm. and lattice.clm. and crystal.clm. and (correspond\$3 match\$3 dangling near10 hydrogenat\$3).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/30 12:09
S225	1	(US-20040164300-\$).did.	US-PGPUB	OR	ON	2008/11/26 10:23
S226	1	S225 and image	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/26 10:23
S227	18	"5759879"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/26 11:31
S228	2	("6380560").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/26 12:07

11/26/2008 2:20:26 PM

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